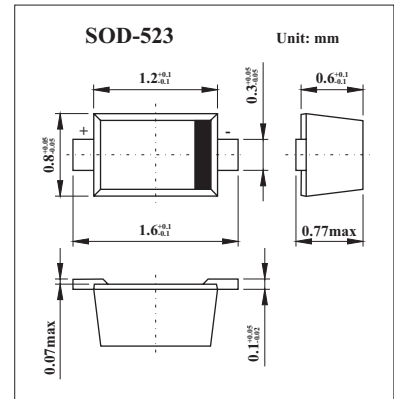


## Silicon Epitaxial Trench Pin Diode

## HVC135



### ■ Features

- Adopting the trench structure improves low capacitance. ( $C=0.6\text{pF max}$ )
- Low forward resistance. ( $r_f=2.0\ \Omega\ \text{max}$ )
- Low operation current.

### ■ Absolute Maximum Ratings $T_a = 25\ ^\circ\text{C}$

Parameter	Symbol	Value	Unit
Peak reverse voltage	$V_{RM}$	65	V
Reverse voltage	$V_R$	60	V
Forward current	$I_F$	100	mA
Power dissipation	$P_d$	150	mW
Junction temperature	$T_j$	125	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +125	$^\circ\text{C}$

### ■ Electrical Characteristics $T_a = 25\ ^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current	$I_R$	$V_R = 60\ \text{V}$			0.1	$\mu\text{A}$
Reverse voltage	$V_F$	$I_F = 2\ \text{mA}$			0.9	V
Capacitance	$C$	$V_R = 1\ \text{V}, f = 1\ \text{MHz}$			0.6	pF
Forward resistance	$r_f$	$I_F = 2\ \text{mA}, f = 100\ \text{MHz}$			2.0	$\Omega$
ESD-Capability *1		$C = 200\text{pF}$ , Both forward and reverse direction 1 pulse	100			V

Note

1. Failure criterion ;  $I_R > 100\ \text{nA}$  at  $V_R = 60\ \text{V}$ .

### ■ Marking

Marking	P5
---------	----